

# GE40N03

## N-CHANNEL ENHANCEMENT MODE POWER MOSFET

BV <sub>DSS</sub>	30V
R <sub>DS(ON)</sub>	17mΩ
I <sub>D</sub>	40A

### Description

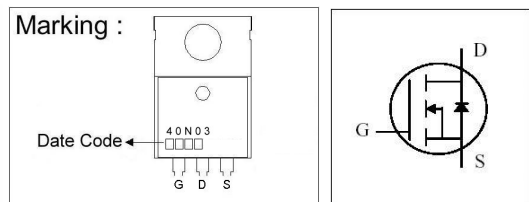
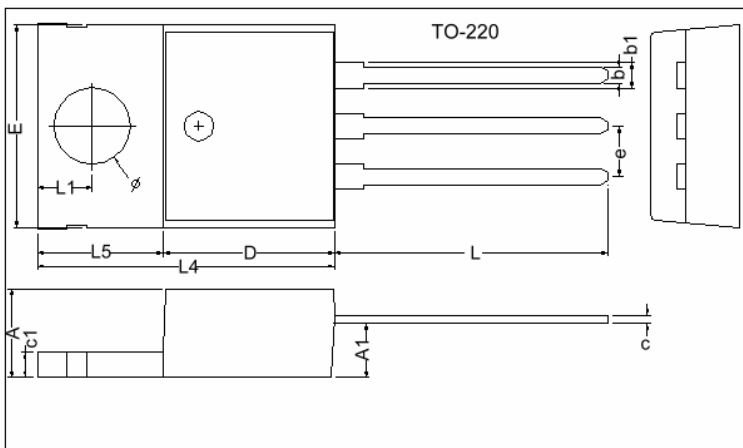
The GE40N03 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications and suited for low voltage application such as DC/DC converters and high efficiency switching circuit.

### Features

- \*Dynamic dv/dt Rating
- \*Simple Drive Requirement
- \*Repetitive Avalanche Rated
- \*Fast Switching

### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	∅	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

### Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> @10V	I <sub>D</sub> @T <sub>C</sub> =25°C	40	A
Continuous Drain Current, V <sub>GS</sub> @10V	I <sub>D</sub> @T <sub>C</sub> =100°C	30	A
Pulsed Drain Current <sup>1</sup>	I <sub>DM</sub>	169	A
Total Power Dissipation	P <sub>D</sub> @T <sub>C</sub> =25°C	50	W
Linear Derating Factor		0.4	W/°C
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 ~ +150	°C

### Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	R <sub>thj-c</sub>	2.5	°C/W
Thermal Resistance Junction-ambient Max.	R <sub>thj-a</sub>	62	°C/W

**Electrical Characteristics (T<sub>j</sub> = 25°C unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> =0, I <sub>D</sub> =250uA
Breakdown Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	-	0.037	-	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	-	3.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA
Forward Transconductance	g <sub>fs</sub>	-	26	-	S	V <sub>DS</sub> =10V, I <sub>D</sub> =20A
Gate-Source Leakage Current	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±20V
Drain-Source Leakage Current(T <sub>j</sub> =25°C)	I <sub>DSS</sub>	-	-	25	uA	V <sub>DS</sub> =30V, V <sub>GS</sub> =0
Drain-Source Leakage Current(T <sub>j</sub> =150°C)		-	-	250	uA	V <sub>DS</sub> =24V, V <sub>GS</sub> =0
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	14	17	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =20A
		-	22	24		V <sub>GS</sub> =4.5V, I <sub>D</sub> =16A
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	-	17	-	nC	I <sub>D</sub> =20A V <sub>DS</sub> =24V V <sub>GS</sub> =5V
Gate-Source Charge	Q <sub>gs</sub>	-	3	-		
Gate-Drain ("Miller") Charge	Q <sub>gd</sub>	-	10	-		
Turn-on Delay Time <sup>2</sup>	T <sub>d(on)</sub>	-	7.2	-	ns	V <sub>DS</sub> =15V I <sub>D</sub> =20A V <sub>GS</sub> =10V R <sub>G</sub> =3.3Ω R <sub>D</sub> =0.75Ω
Rise Time	T <sub>r</sub>	-	60	-		
Turn-off Delay Time	T <sub>d(off)</sub>	-	22.5	-		
Fall Time	T <sub>f</sub>	-	10	-		
Input Capacitance	C <sub>iss</sub>	-	800	-	pF	V <sub>GS</sub> =0V V <sub>DS</sub> =25V f=1.0MHz
Output Capacitance	C <sub>oss</sub>	-	380	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	133	-		

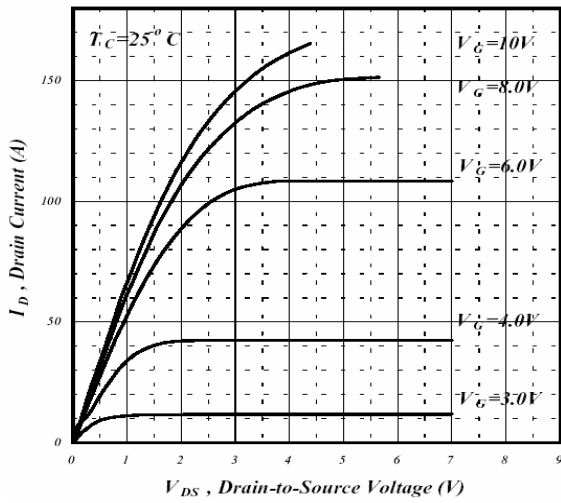
**Source-Drain Diode**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage <sup>2</sup>	V <sub>SD</sub>	-	-	1.3	V	I <sub>S</sub> =40A, V <sub>GS</sub> =0V, T <sub>j</sub> =25°C
Continuous Source Current (Body Diode)	I <sub>S</sub>	-	-	40	A	V <sub>D</sub> =V <sub>G</sub> =0V, V <sub>S</sub> =1.3V
Pulsed Source Current (Body Diode) <sup>1</sup>	I <sub>SM</sub>	-	-	169	A	

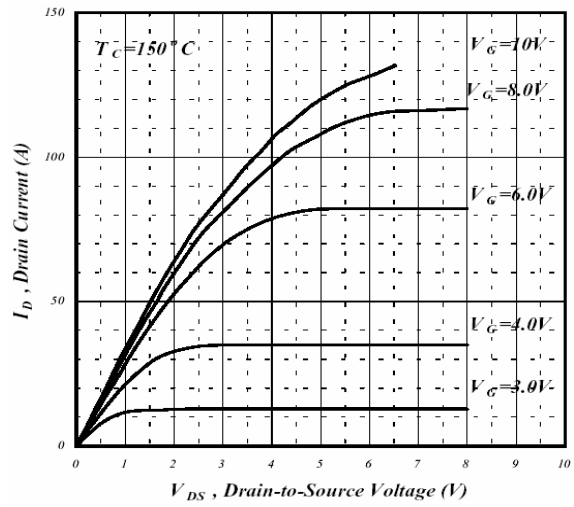
Notes: 1. Pulse width limited by safe operating area.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

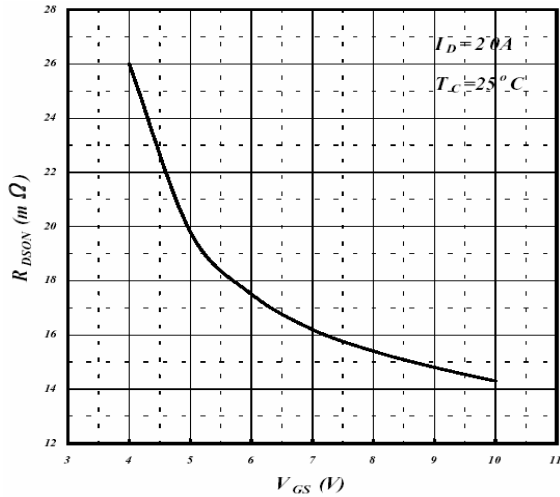
## Characteristics Curve



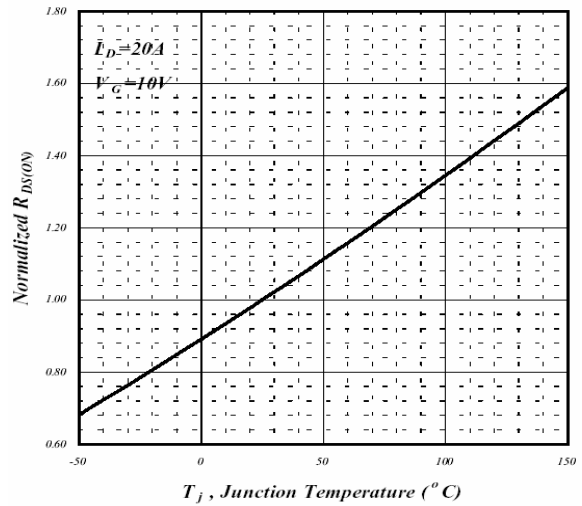
**Fig 1. Typical Output Characteristics**



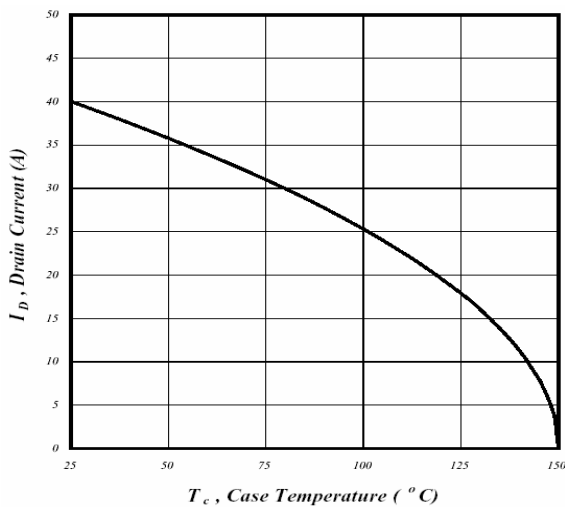
**Fig 2. Typical Output Characteristics**



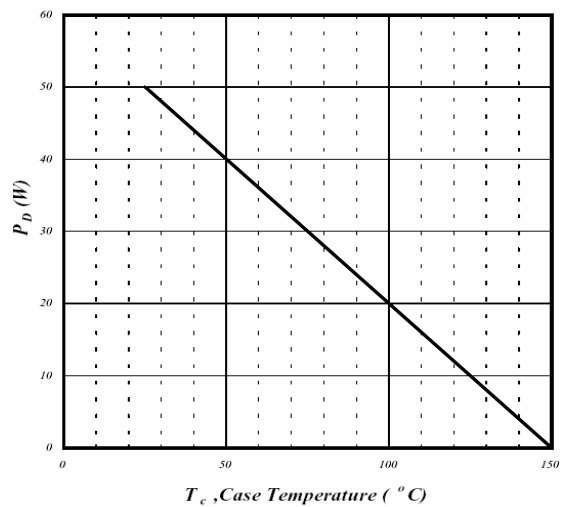
**Fig 3. On-Resistance v.s. Gate Voltage**



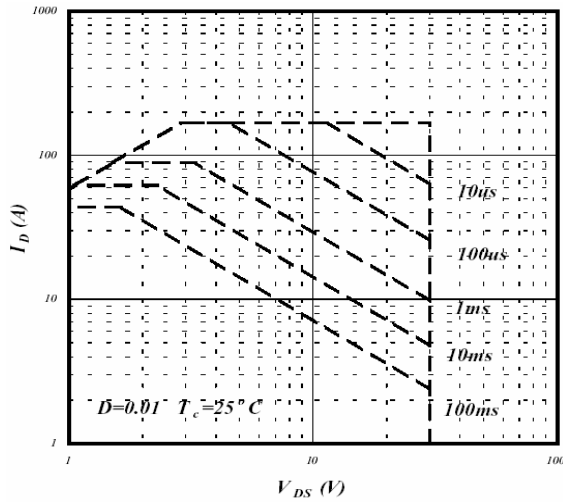
**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



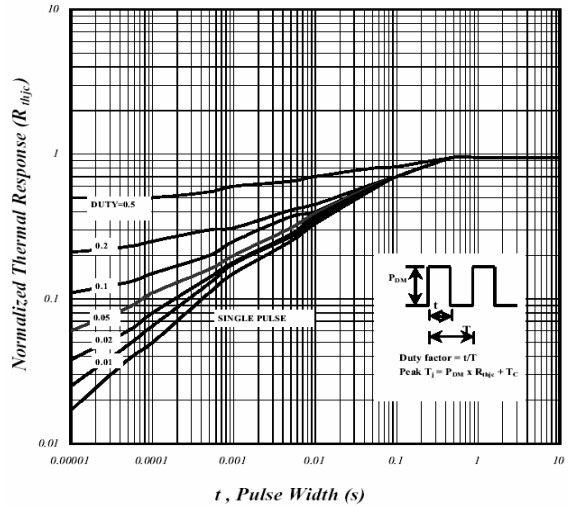
**Fig 5. Maximum Drain Current v.s. Case Temperature**



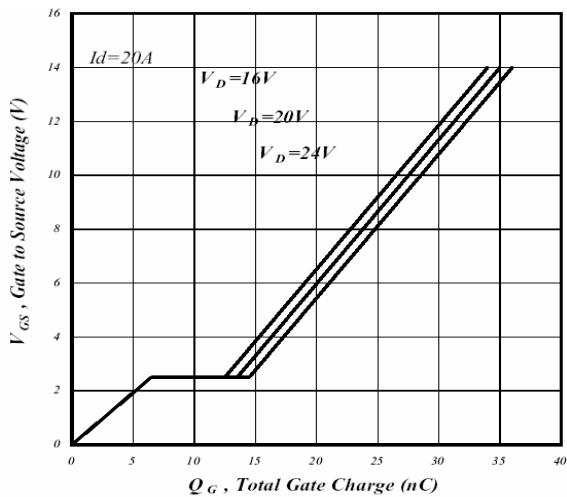
**Fig 6. Type Power Dissipation**



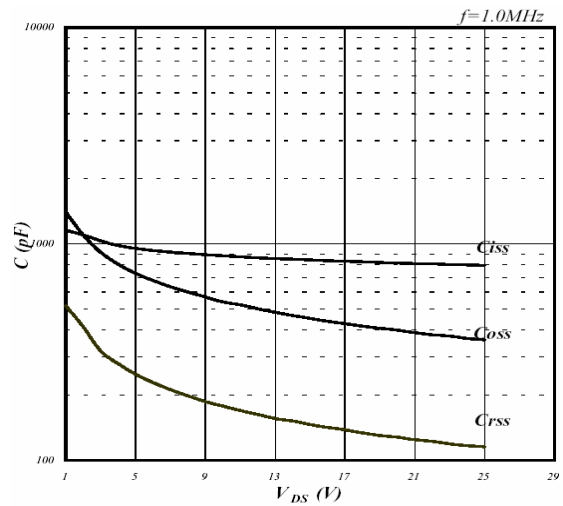
**Fig 7. Maximum Safe Operating Area**



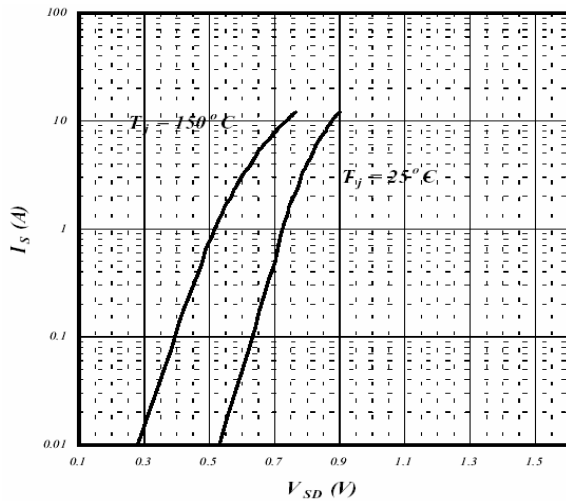
**Fig 8. Effective Transient Thermal Impedance**



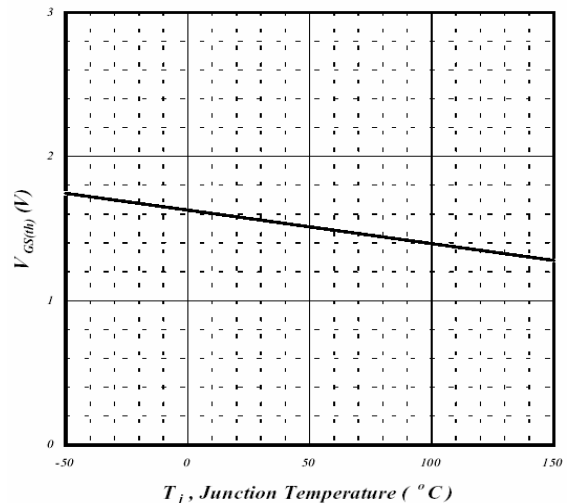
**Fig 9. Gate Charge Characteristics**



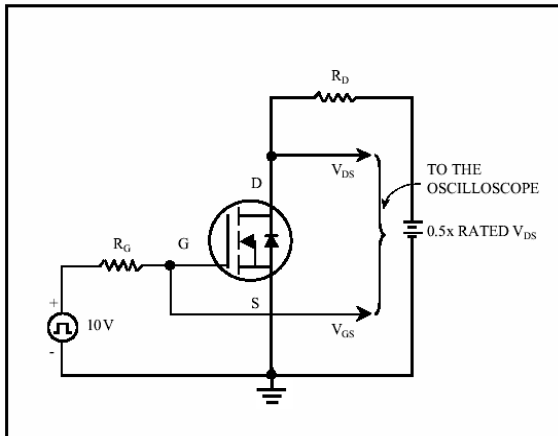
**Fig 10. Typical Capacitance Characteristics**



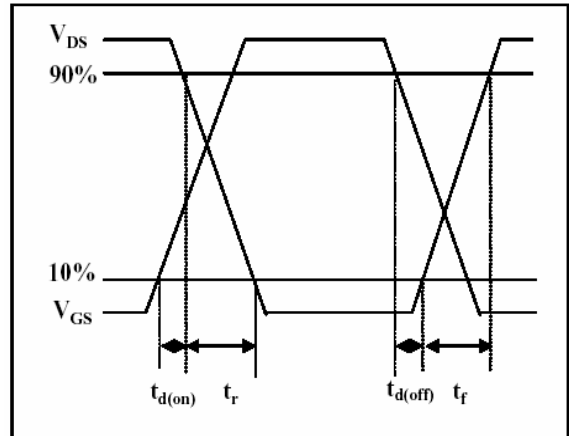
**Fig 11. Forward Characteristics of Reverse Diode**



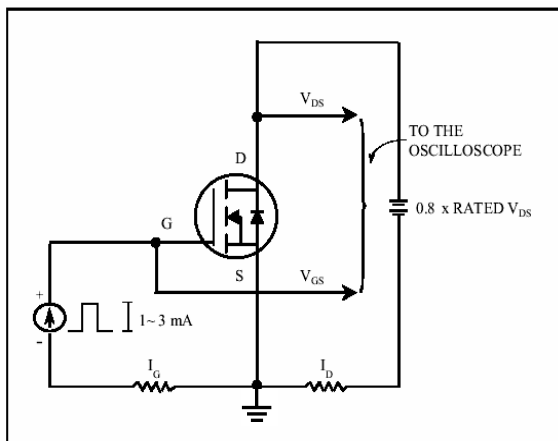
**Fig 12. Gate Threshold Voltage v.s. Junction Temperature**



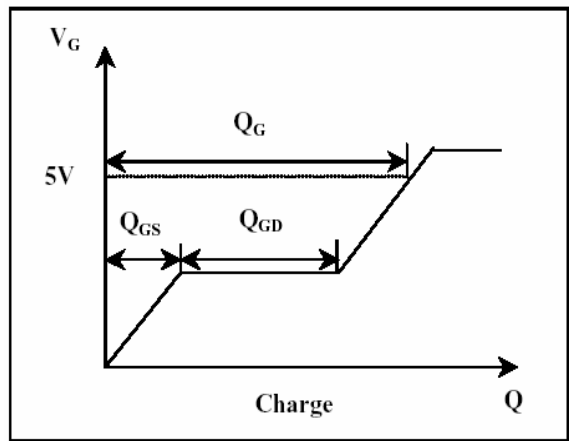
**Fig 13. Switching Time Circuit**



**Fig 14. Switching Time Waveform**



**Fig 15. Gate Charge Circuit**



**Fig 16. Gate Charge Waveform**

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